

Allpix² 的像素探测器电荷收集模拟

- 基于Geant4 确定入射粒子沉积 & 收集 信号范围

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入射粒子 (MIPS) 的电荷收集分析

■ MIP粒子 收集电荷分布: 3GeV Proton

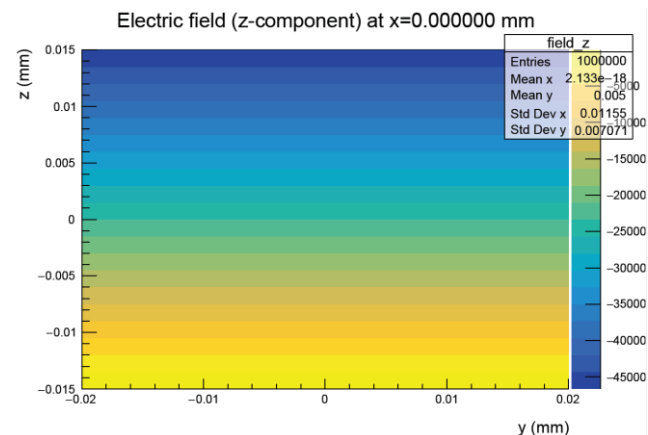
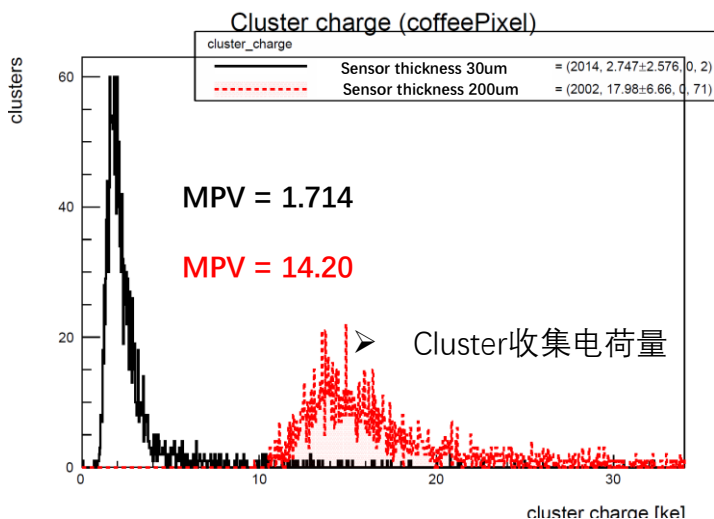
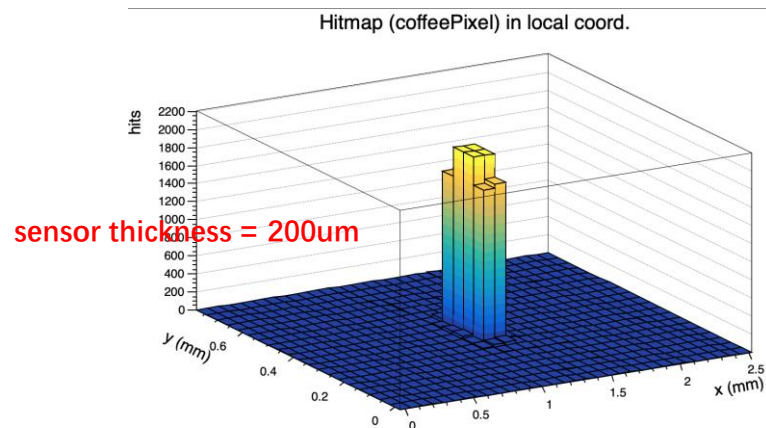
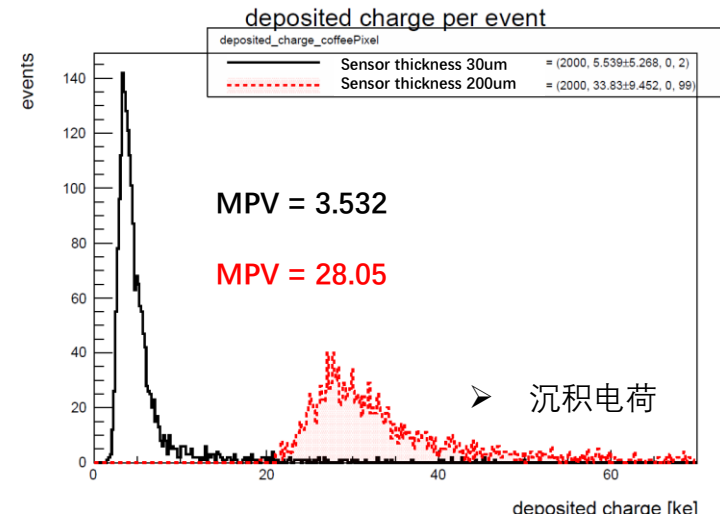
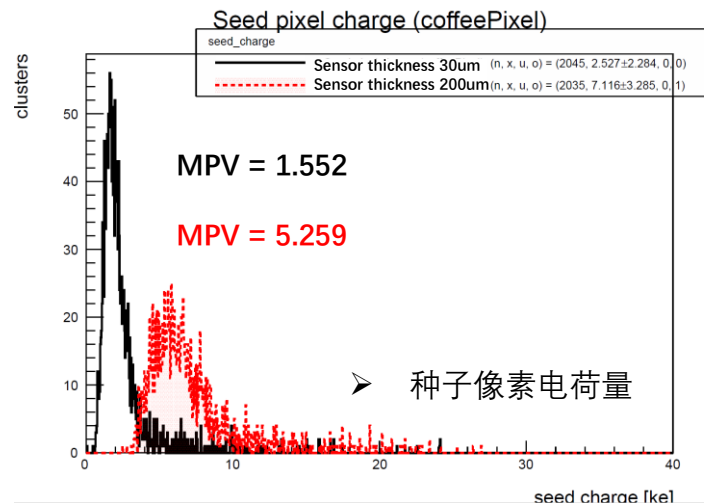
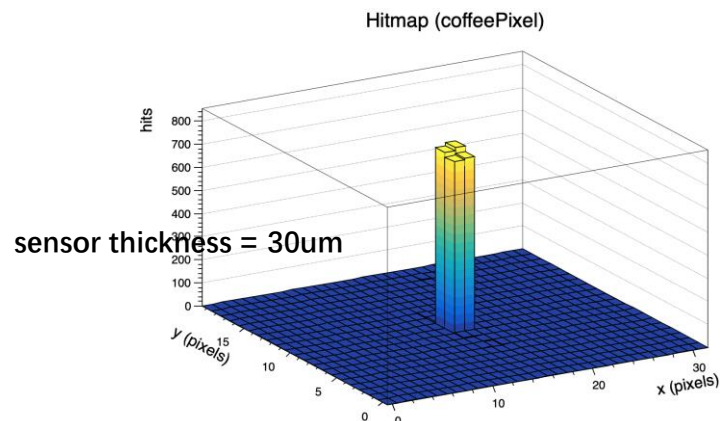
sensor thickness = 30/200um

Depletion depth = 30um

Bias voltage = 70V

- 进一步精确模拟 需要从TCAD导入对应得电场分布和掺杂浓度分布文件 (e.g. Epi: $1.68e^{15}/cm^3$ [$8\Omega \cdot cm$]; Sub: $1.34e^{21}/cm^3$, 该工艺未知)

- 模拟MIP粒子穿透芯片;
 - $Landau \otimes Gauss$ or Landau or Gauss
- The most probable value of landau or mean



入射粒子 (MIPS) 的电荷收集分析

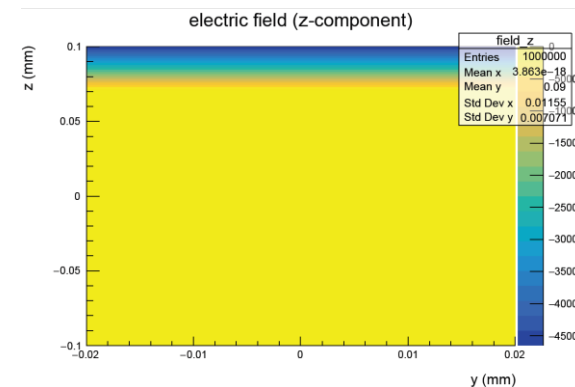
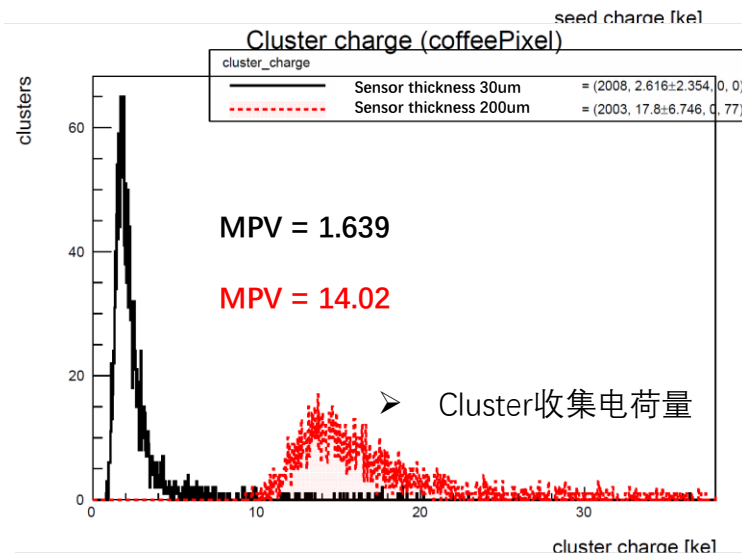
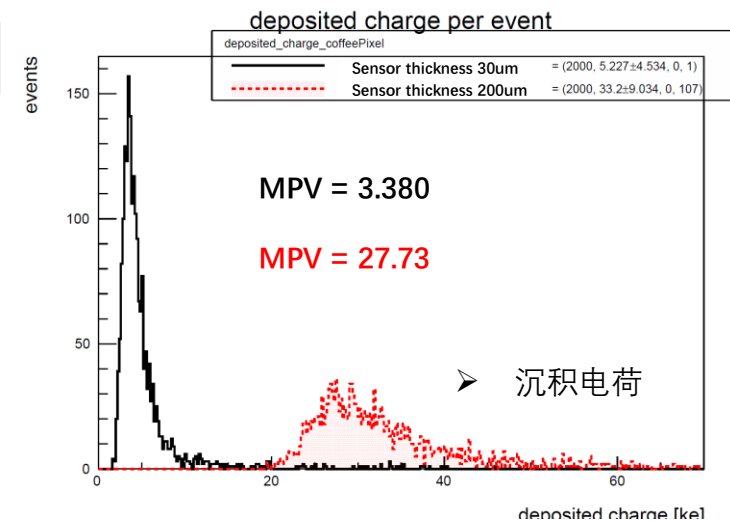
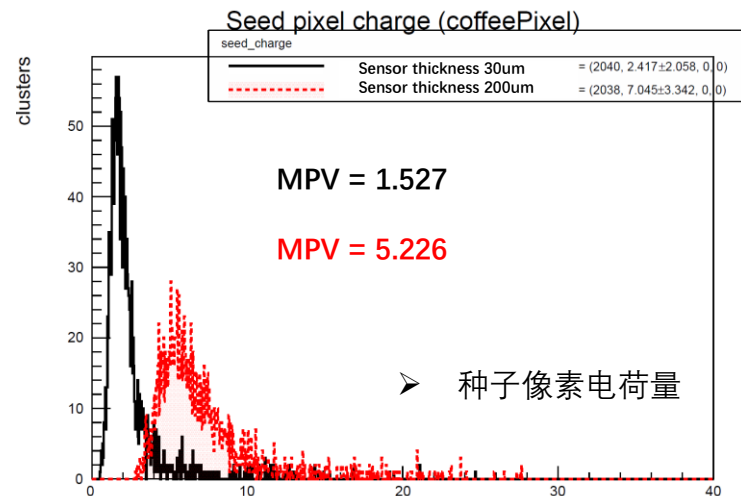
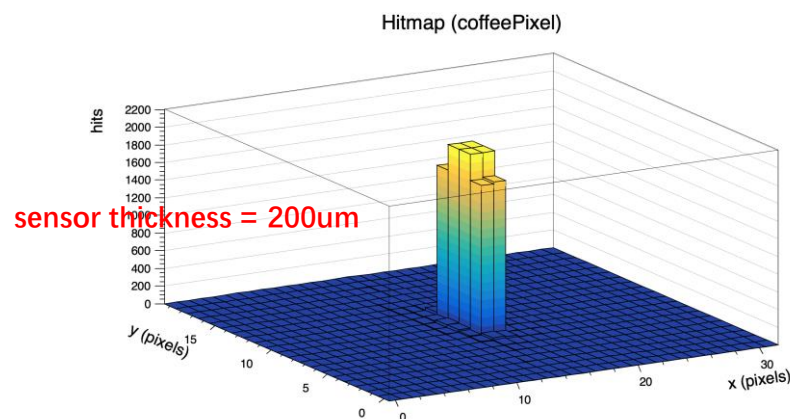
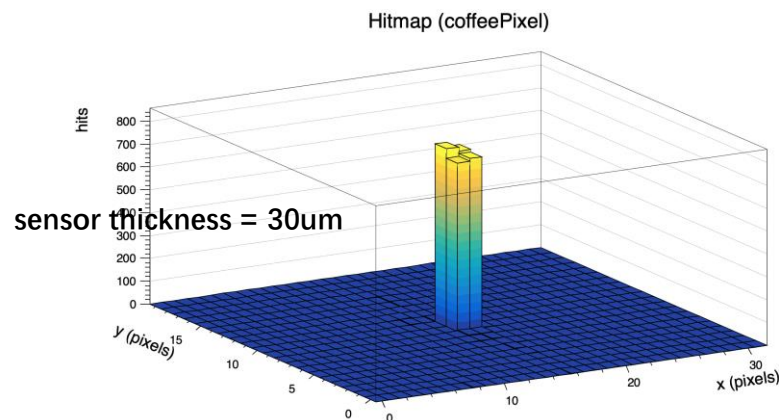
■ MIP粒子 收集电荷分布: 350MeV Muon

sensor thickness = 30/200um

Depletion depth = 30um

Bias voltage = 70V

- 模拟MIP粒子穿透芯片;
 - *Landau* $\otimes$ *Gauss* or Landau or Gauss
- The most probable value of landau or mean



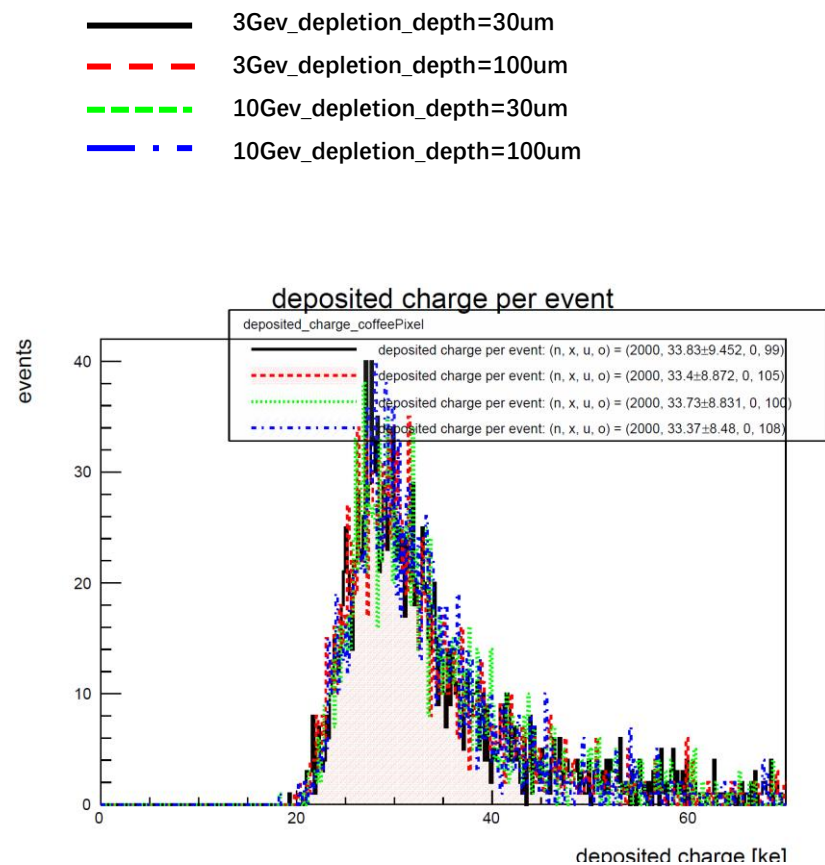
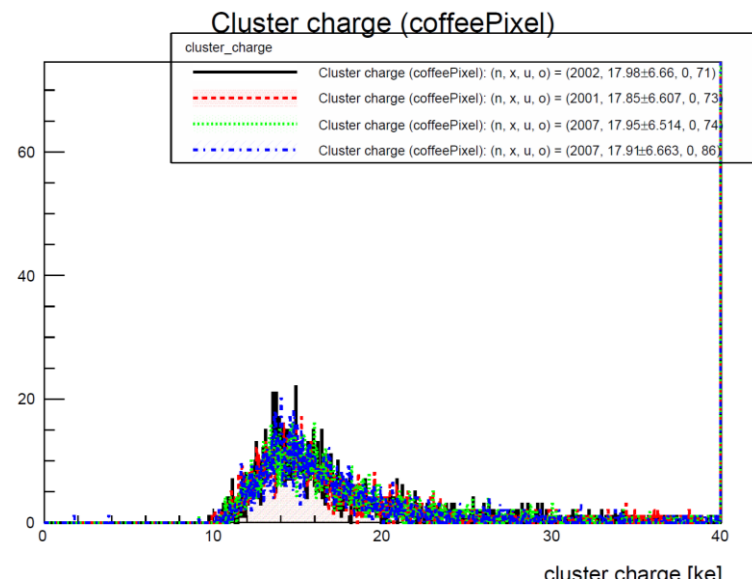
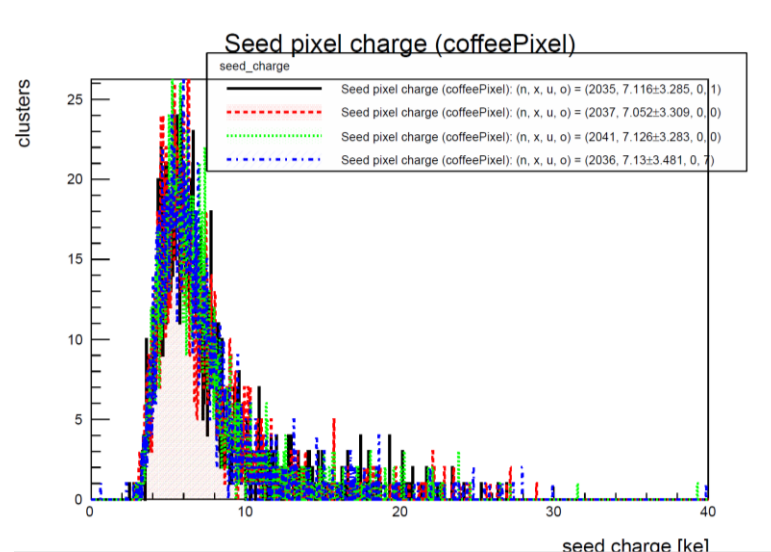
入射粒子（MIPS）的电荷收集分析

■ MIP粒子 收集电荷分布： 3GeV / 10GeV Proton

sensor thickness = 200um

Depletion depth = 30um / 100um

Bias voltage = 70V



$CCE = \text{Collect Charge}_{MPV} / \text{Deposited}_{MPV}$ 约为50%

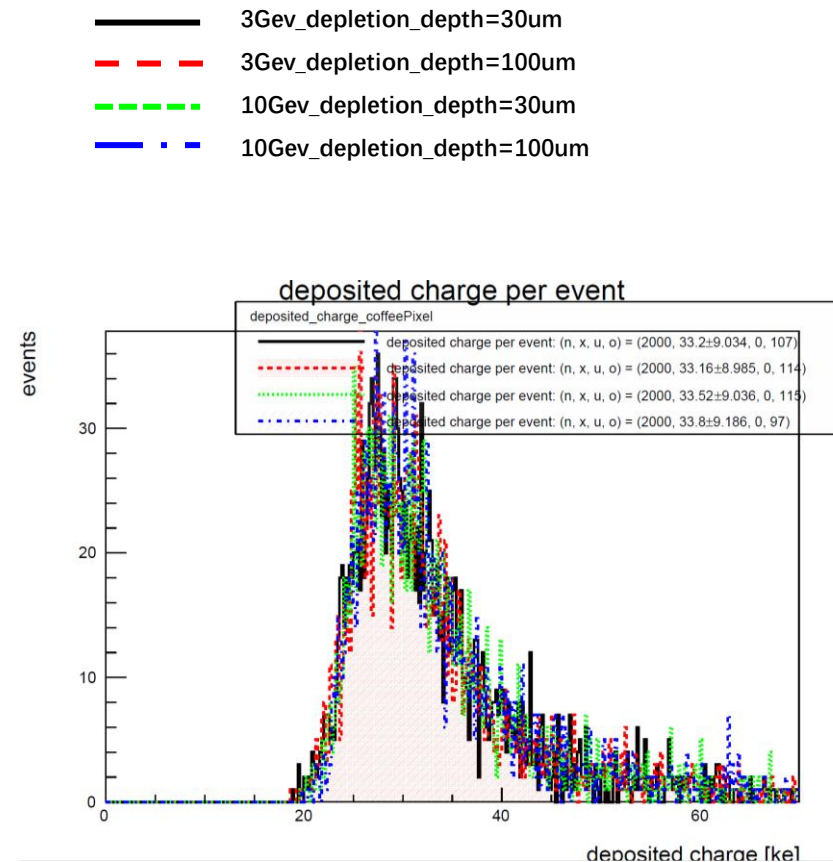
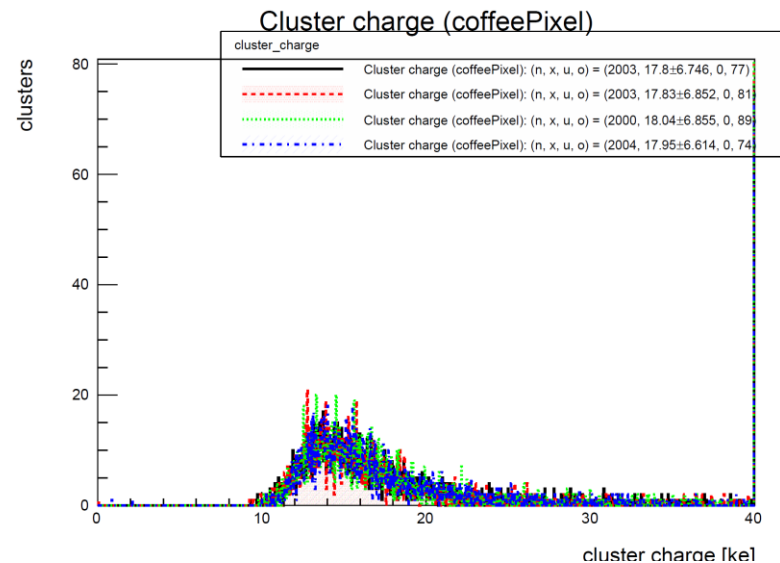
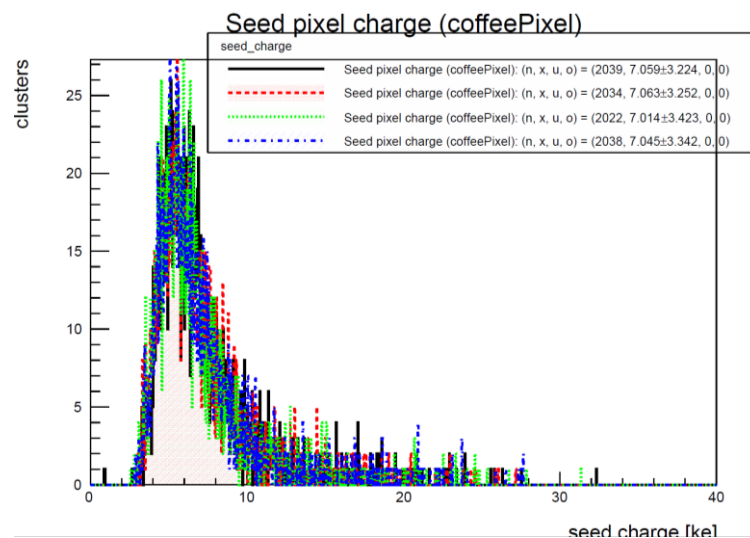
入射粒子 (MIPS) 的电荷收集分析

■ MIP粒子 收集电荷分布: 350MeV / 1GeV Muon

sensor thickness = 200um

Depletion depth = 30um / 100um

Bias voltage = 70V



$CCE = Collect\ Charge_{MPV} / Deposited_{MPV}$ 约为50%

Back up

■ 几何模型的搭建model

- 单片式像素探测器: monolithic
- 像素数量: 100×100 ;
- 像素阵列的间距: 50um 50um;
- 外延层厚度: 5um;
- 衬底厚度: 50um;

■ 物理过程

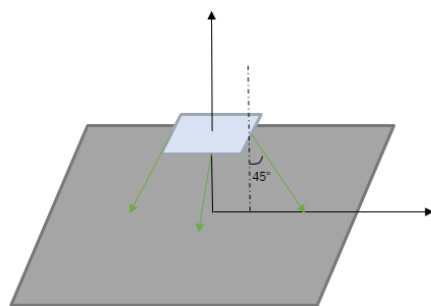
- physics_list = FTFP_BERT_LIV;

■ 粒子源设置

- A. 中心为像素阵列上方 (0, 0, 1) mm;
- 粒子源为50um*50um的正方形平面;
 - 各向同性发射;
 - θ 角为 $0 \sim 45^\circ$ && ϕ 角为 $0 \sim 360^\circ$;
- B. 位置为像素阵列上方 (0, 0, 0.5) mm;
- 种类为 Fe55放射源;

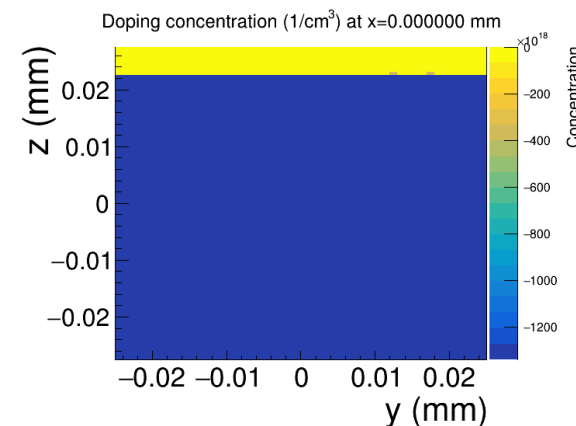
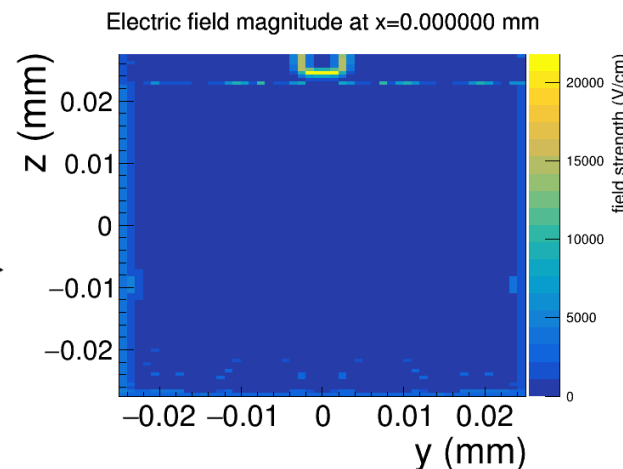
■ 电场分布

- 从TCAD中导入对应的电场分布文件;



■ 掺杂浓度分布

- 从TCAD中导入对应的掺杂浓度分布文件;
- (Epi: $1.68e^{15}/cm^3$ [$8\Omega \cdot cm$]; Sub: $1.34e^{21}/cm^3$)



■ 载流子传播 (manual 6.2&6.3)

- 设置的传感器温度: 300K
- 载流子迁移率模型: masetti_canali (与掺杂浓度相关)
- 载流子寿命&复合模型: srh_auger (与掺杂浓度相关)